

Nikolai Yarykin

List of Publications by Year in descending order

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papers

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docs citations

24
times ranked

79
citing authors

#	ARTICLE	IF	CITATIONS
1	On the nature of hydrogen-related centers in p-type irradiated silicon. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 210-212.	2.7	27
2	Contribution of the disturbed dislocation slip planes to the electrical properties of plastically deformed silicon. <i>Physica B: Condensed Matter</i> , 2003, 340-342, 1005-1008.	2.7	23
3	Copper-related deep-level centers in irradiated p-type silicon. <i>Physical Review B</i> , 2011, 83, .	3.2	20
4	Evidence for room-temperature in-diffusion of nickel into silicon. <i>Applied Physics Letters</i> , 2016, 109, 102101.	3.3	14
5	Deep levels of copper-hydrogen complexes in silicon. <i>Physical Review B</i> , 2013, 88, .	3.2	12
6	The Electrical Activity of Dislocation Slip Planes in Semiconductor Crystals. <i>Materials Science Forum</i> , 1986, 10-12, 787-790.	0.3	8
7	Nickel in silicon: Room-temperature in-diffusion and interaction with radiation defects. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017, 14, 1700005.	0.8	6
8	Properties and identification of the oxygen-related radiation defects in silicon. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 483-486.	2.7	5
9	Metastable Cu$\&V\&O^*$ Complex in Silicon. <i>Solid State Phenomena</i> , 0, 205-206, 255-259.	0.3	5
10	Hydrogenation of the CuPL center in silicon. <i>Applied Physics Letters</i> , 2014, 105, 012109.	3.3	5
11	Spatial Distribution of the Dislocation Trails in Silicon. <i>Solid State Phenomena</i> , 2015, 242, 155-159.	0.3	5
12	The Cu photoluminescence defect and the early stages of Cu precipitation in Si. <i>Journal of Applied Physics</i> , 2020, 127, .	2.5	5
13	Dislocation trails in Si: Geometry and electrical properties. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017, 14, 1700074.	0.8	5
14	Interaction of Interstitial Copper with Isolated Vacancies in Silicon. <i>Solid State Phenomena</i> , 0, 242, 308-311.	0.3	4
15	Electrically Active Copper-Nickel Complexes in p-Type Silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900304.	1.8	4
16	Oxygen gettering at defects introduced by plastic deformation in silicon. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 3070-3074.	0.8	3
17	Room-temperature Ni Interaction with Deformation-Induced Defects in Si: A DLTS Study. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2019, 216, 1900326.	1.8	3
18	Deep level centers in electron-irradiated silicon crystals doped with copper at different temperatures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017, 14, 1600267.	0.8	3

#	ARTICLE	IF	CITATIONS
19	DLTS study of the oxygen dimer formation kinetics in silicon. <i>Physica B: Condensed Matter</i> , 2009, 404, 4576-4578.	2.7	2
20	Nickel Interaction with Vacancy-Type Radiation Defects in Silicon. <i>Physica Status Solidi - Rapid Research Letters</i> , 2019, 13, 1800651.	2.4	2
21	Centers with low correlation energy in deep-level transient spectroscopy studies. <i>Semiconductor Science and Technology</i> , 2008, 23, 125031.	2.0	1
22	Interstitial Carbon in p -Type Copper-Doped Silicon. <i>Solid State Phenomena</i> , 0, 242, 302-307.	0.3	1
23	Copper Complexes with Carbon-Related Radiation Defects in Silicon. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 0, , 2100141.	1.8	1
24	Electrical Activation of Interstitial Ni in Cu-Doped Si. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 0, , 2100135.	1.8	0